

# Thermoelectric Material Library via Laser Melting

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## **Research Highlights**

- Rapid synthesis of thermoelectric compounds via laser melting is successfully applied to binary, ternary and • quaternary systems.
- Thermoelectric properties of the compounds reasonably agree with literature.
- Process time of the laser melting requires 2-3 min/sample, and 20 samples/batch is available.

## Laser Melting System and Synthesized Compounds

## Laser Melting Apparatus



[Laser specification] Semiconductor laser

Operation Mode : CW

Laser Power: 0 - 70W

350

300

250

200

150 100

0 1

(Hamamatsu Photonics, LD-HEATER)

Temperature monitoring range (two-color method): 200 - 800°C

Fig. Heating characteris various metals illuminated by a laser diode. The inset shows the saturated maximum temperature (T) under continuous laser rradiation with a certain power (F De slows (ATLO))

The slope  $(\Delta T/\Delta P)$  is plotted as a unction of light absorptance (a)

Wavelength : 940nm±20nm (at 30W),

Spot Size: 1.2mm (at WD of 90mm)

0.2 0.3 0.4 0.5

## **Process Flow of TE Library**



#### [Powder weighing] Semi-automated weighing system (Alpha, Japan) ccuracy ±1 mg Process time within 1 min for 1 g weighing

[Installing] Manual process Pelletizing into d 3 x h 5 mm<sup>2</sup> or pouring into Al<sub>2</sub>O<sub>3</sub> crucible (di:4.6mm)

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Install pellets in the chamber
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Gas replacement or evacuation, if required

#### [Laser melting] [Specimen mounting]

[Grinding and polishing]



[TEP measurement] Thermopower and resistivity are measured using prober system. Base temperature is controllable with Peltier stage.

Thermal effusivity is reflectance method (FDTR, Bethel Japan) after Mo sputtering.

## Laser melted materials (examples)



## **Thermoelectric Properties**





## Mn-Al-Si

20

10

-10 S / µVK -20 -30

-40

-50

-60



at RT

## Ba-Ga-Al-Si (clathrate)











Rapid synthesis of thermoelectric compounds by laser melting 7. Kinemuchi, M. Mikami, I. Terasaki, W. Shin, Materials and Design 106 (2016) 30-36

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